

# Panel Fan-Out Manufacturing: Why, When, How? The Jury Has Convened

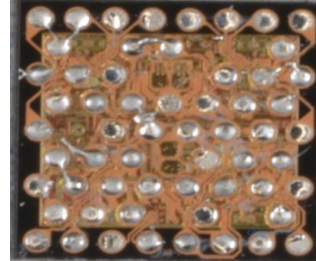


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# Example of FOWLPs in Smartphones



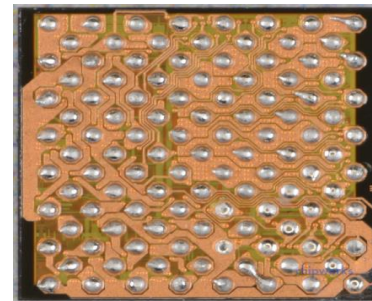
Qualcomm RF transceiver  
Package is 3.3 mm x 3.3 mm



Qualcomm PMIC  
5.4 mm x 5.4 mm  
part also found

Source: ChipWorks.

Qualcomm Audio CODEC  
Package is 4.25 mm x 3.90 mm

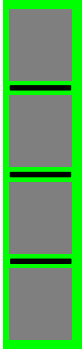
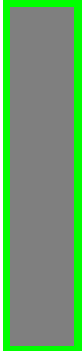
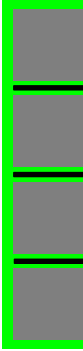

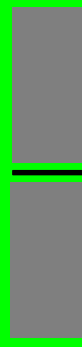

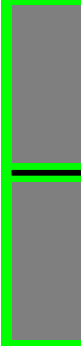


Source: ChipWorks.

- **FO-WLPs in many Smartphones**
  - Samsung models'
  - Huawei models'
  - Xiaomi models'
- **Parts from Qualcomm using WLB process**

# Example of Scaling in Package Assemble

- Growth of Substrate Strips to Leverage Batch Processing Economics

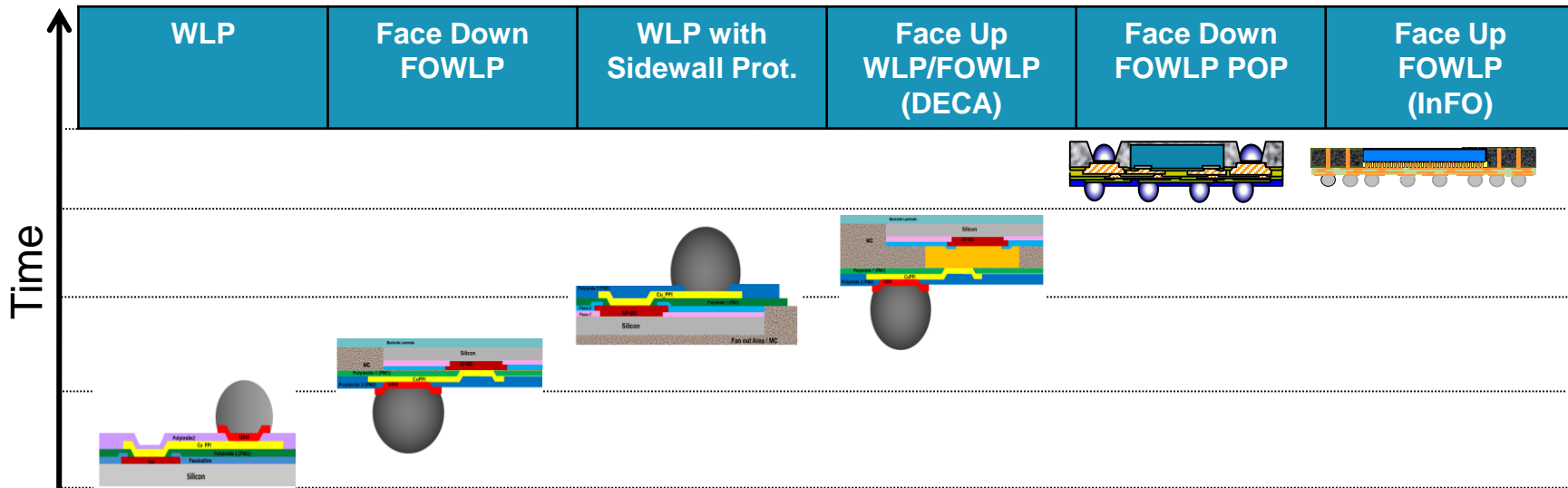
SAT	Low Density		High Density				Ultra High Density 2-Up
	4-up	1-up	4-up	3-up	2-Up	1-up	2-Up
							
A	62x230mm	-	-	74x240mm	-	-	95x240.5mm
B	63.45x240mm	63.45x240mm	-	-	-	72.6x240mm	
C	60x220mm	-	74x240mm	-	-	74x240mm	
D	63x240mm	-	-	-	-	73.6x241mm	

Packages per batch operation increasing,

→ Utilization of Panel Increasing

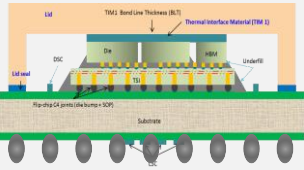
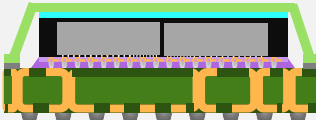
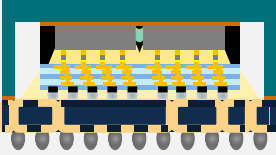
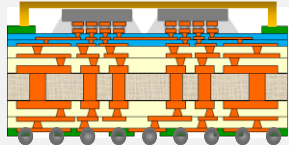
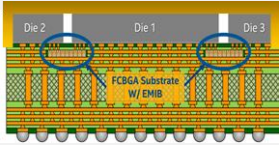
→ Cost Advantage

# Wafer Processed Package Evolution



	WLP	Face Down FOWLP	WLP with Sidewall Prot.	Face Up WLP/FOWLP (DECA)	Face Down FOWLP POP	Face Up FOWLP (InFO)
<b>Features and Benefits</b>	<ul style="list-style-type: none"> <li>- Lowest cost solution if applicable</li> <li>- Finer pitch routing than substrates</li> </ul>	<ul style="list-style-type: none"> <li>- Cost effective for die requiring some fan out</li> <li>- Lower parasitics</li> <li>- Finer pitch routing than substrates</li> </ul>	<ul style="list-style-type: none"> <li>- More robust handling, Not prone to edge cracking</li> </ul>	<ul style="list-style-type: none"> <li>- Flat surface to pattern RDL. Finer pitch possible</li> <li>- Mold protection over die surface</li> </ul>	<ul style="list-style-type: none"> <li>- Thinner POP possible compared to substrate based</li> </ul>	<ul style="list-style-type: none"> <li>- Flat surface for patterning RDL. Finer pitch Pillars for POP connection than solder balls</li> </ul>
<b>Challenges</b>	<ul style="list-style-type: none"> <li>- Rel limits die size</li> <li>- Handling issues for EMS</li> <li>- Low K challenged</li> </ul>	<ul style="list-style-type: none"> <li>- 2+ layers of RDL more expensive than substrate pkg.</li> </ul>	<ul style="list-style-type: none"> <li>- Increases cost over WLP</li> </ul>	<ul style="list-style-type: none"> <li>- Requires growth of Cu pillar on die</li> </ul>	<ul style="list-style-type: none"> <li>- Cost For 2+ RDL</li> </ul>	<ul style="list-style-type: none"> <li>- Cost for 2+ RDL</li> <li>- Cost to grow Cu pillars for POP</li> </ul>
<b>Applications</b>	<ul style="list-style-type: none"> <li>- Devices that I/O boundary</li> </ul>	<ul style="list-style-type: none"> <li>- Alternative to FC for many apps</li> <li>- Multi chip modules</li> </ul>	<ul style="list-style-type: none"> <li>- Same as WLP</li> </ul>	<ul style="list-style-type: none"> <li>- Same as FOWLP, WLP, sidewall protected WLP</li> </ul>	<ul style="list-style-type: none"> <li>- Apps processor for high end phones</li> </ul>	<ul style="list-style-type: none"> <li>- Apps processor for high end phones</li> </ul>

# 2.1/2.5D Advanced Packages for Multichip, Processors, GPUs and FPGA – Opportunities for FO Packaging

	2.5D			2.1D	
	TSI CoWoS, CoW, CoS	FOCoS Fan Out Chip on Substrate	SWIFT (Die last FO)	2.1D Photo- Defined Organic Interposer (POI)	EMIB
					
<b>Suppliers</b>	TSMC, Multiple OSATS	ASE	Amkor	Shinko	Intel
<b>Features</b>	<ul style="list-style-type: none"> <li>• Si Interposer</li> <li>• Glass Interposers for electrical performance by GaTech</li> <li>• Die first or last assembly depending on process flow</li> <li>• In LVM</li> </ul>	<ul style="list-style-type: none"> <li>• Die first face down FO construction</li> <li>• Leverages HVM processes of standard FOWLP but fine pitch RDL</li> <li>• In Dev.</li> <li>• Panel possible</li> </ul>	<ul style="list-style-type: none"> <li>• Die last</li> <li>• Conventional RDL</li> <li>• Die last assembly</li> <li>• AOI inspected RDL</li> <li>• In Dev.</li> <li>• Panel possible</li> </ul>	<ul style="list-style-type: none"> <li>• Advanced PID Substrate</li> <li>• Die last assembly</li> <li>• AOI Inspected RDL</li> <li>• In Dev.</li> <li>• Larger panel possible</li> </ul>	<ul style="list-style-type: none"> <li>• Si Bridge Embedding</li> <li>• Laser SRO/ Mixed Bump</li> <li>• Known Good Si Bridge</li> <li>• Combination of 300mm and larger panel</li> <li>• In LVM</li> </ul>
<b>Assembly Complexity</b>	Si Interposer +Substrate Assembly	FO processes+ PKG to Substrate Assembly	RDL+ Chip Joining + PKG to Substrate Assembly	Conventional Chip Joining only	Conventional Chip Joining only

# FOWLP and the Quest for Smaller Form Factor, Higher Integration, and Larger Panels

- Eliminates die interconnect (bump & wire bonds) and substrate
  - Finer pitches than substrate based technology
  - 10-15um L/S common, 5/5um in HVM, ~2/2um L/S in LVM
  - Shorter interconnects = Lower parasitic
  - Eliminate interconnect stress and ELK crack delamination issues
  - Can improve thermal characteristics
- Batch packaging process like WLP
  - Can use KGD
  - Round panels can leverage WLP and FC bumping equipment
  - Square panels can leverage material and process understanding from WLP
- Potential SiP, Multi-die, 3D Solution
- Larger panel batch processing in development to lower cost
  - Challenges in patterning, sputtering, plating, and materials
  - Challenges with metrology over large format